

1993 FALL MEETING GENERAL INFORMATION

■ Location/Lodging

Boston Marriott/ Copley Place

110 Huntington Avenue Boston, MA 02116 (800) 228-9290 (617) 236-5800 (Direct) Fax (617) 236-5885 Rate: \$114/Single \$128 Double

Westin Hotel/ Copley Place

10 Huntington Avenue Boston, MA 02116 (800) 228-3000 (617) 262-9600 (Direct) Fax (617) 424-7483 Rate: \$118/Single \$143 Double

Travel Arrangements

The official travel management company for the Materials Research Society's 1993 Fall Meeting is Giselle's Travel Bureau. They will guarantee the lowest fares on any airline at time of booking. Call Giselle's and ask for MRS Group 001: 1-800-782-5545

Monday - Friday, 7:30 a.m. - 5:30 p.m. PST

FAX: (916) 927-0454 or 1-800-TRVLFAX

MRS meeting attendees receive the following travel benefits and services:

Lowest fares on any airline guaranteed • Free flight insurance of \$100,000 • Vouchers for discounts on vacation packages • Car rental savings • Computerized driving instructions from Logan International Airport to your hotel.

ONE MRS MEETING ATTENDEE WILL WIN TWO (2) FREE AIRLINE TICKETS TO ANYWHERE IN THE 48 UNITED STATES.

To be eligible: You, your travel agent, or your in-house travel department must make your reservations through Giselle's Travel Bureau by calling the above phone number.

Local Transportation

Shuttle service to the Boston Marriott and Westin Hotels from Logan International Airport departs every half-hour from the designated shuttle stop in front of each terminal. The cost is approximately \$6-\$8 one way. Cab fares range between \$15-\$17 per ride (up to four persons can share one cab).

There is a free shuttle from airport terminals to the airport subway station (The "T"). Copley Station is within one block of the Marriott, Westin, and alternative hotels on the "Green Line."

Parking

A parking garage is adjacent to both hotels at a daily cost of approximately \$21.

DEADLINE FOR HOTEL RESERVATIONS: NOVEMBER 1, 1993

Blocks of rooms have been reserved for MRS meeting attendees at the Boston Marriott and Westin Hotels (above) and at the alternative hotels (below) located within a one-block radius. When making your reservations at any hotel, mention the Materials Research Society to receive the special rates.

Alternative Housing

The Colonnade

Phone: (617) 424-7000 Fax: (617) 424-1717 Rate: \$130/Single-Double

Sheraton Boston Hotel & Towers

Phone: (617) 236-2000 Fax: (617) 236-1702

\$109/Single; \$119/Double Rate:



MRS Short Coursel **Tutorial** Program

The Lenox Hotel

Phone:

Fax:

Rate:

(617) 536-5300 (617) 266-7905

\$100/Single

\$110/Double

Characterization of Materials

Modern Materials Analysis Techniques

Instructors: James A. Borders, Kenneth H. Eckelmeyer, and Michael R. Keenan C-03

Surface and Thin Film Analysis Instructors: James W. Mayer and Leonard C. Feldman

Scanning Tunneling Microscopy and Atom Force Microscopy Instructor: Dawn A. Bonnell

C-20 Optical Characterization of III-V Semiconductor Epitaxial Layers

X-Ray Diffraction Characterization of Semiconductor Wafers

Instructors: Mary Halliwell and Isabella Bassignana

Practical Electron Diffraction Instructor: Ronald M. Anders

C-30 Characterization of the Morphology, Structure and Properties of Inorganic Thin New! Instructors: Alton D. Romig, Jr., and Donald M. Mattox

Super-Resolution Imaging and Spectroscopy with Near-Field Scanning Optical

Microscopy (NSOM)
Instructors: Michael Paesler and Hans Hallen New!

Preparation and Fabrication of Materials

Plasma Etching for Microelectronic Fabrication

Instructor: G. Kenneth Herb

Fundamentals and Applications of Ion Beam Assisted Deposition Instructor: James K. Hirvone

P-02

Molecular Beam Epitaxy Instructor: L. Ralph Dawson

Film Formation, Adhesion, and Surface Preparation Instructor: Donald M. Mattox P-04

Metalorganic Chemical Vapor Deposition and Atomic Layer Epitaxy

Chemical Vapor Deposition for Metallization Applications

Instructors: Mark J. Hampden-Smith and Toivo T. Koda New!

Metallization for Devices, Circuits, and Packaging and in Multilayer Schemes for VLSI and ULSI Instructor: Shyam P. Murarka New!

Advanced Materials

M-15 Biological Processes for Materials Synthesis Instructor: Mark Alper

Ferroelectric Thin Films

Instructors: Angus I. Kingon and Seshu B. Desu M-19 Wide Bandgap II-VI Semiconductor Microstructures: Growth, Characterization, and Optical Devices

New! Instructor: Leslie A. Kolodziejski

Techniques

Plasma Technology for Thin Film Deposition Instructor: Donald M. Mattox

Tutorial Program

MRS Tutorials are designed to inform individuals about subjects that are outside their immediate interest or to bring individuals "up to speed" in an area that they have recently entered.

TP-1 Transfer of Technology from R&D to Manufacturing Instructors: Donald M. Mattox and Alton D. Romig, Jr.

Fractals in Materials Science

Instructor: James E. Martin

TP-3 Fullerenes

Instructors: Mildred S. Dresselhaus and Peter C. Eklund

Ne_Mj₂ Lbj₂ Light-Emitting Porous Silicon: Fabrication, Properties, and Device Applications Instructor: Phillipe M. Fauchet

Challenges in Design and Processing of Materials by Biomimetics Instructors: Mehmet Sarikaya, David A. Tirrell, Eric Baer, and Ilhan A. Aksay New!

Special Discounts

There are special discounted tuition fees for specific course combinations. Facilities registering three or more persons at the same time in one MRS Short Course receive a 20% discount for the third and all additional persons.

On-Site Short Course Program

Most MRS courses are available on a contract basis for presentation at your facility. For further details, contact Vivienne Harwood Mattox, MRS Short Course Manager. Telephone (505) 294-9532; Fax (505) 298-7942

Registration Information

Call (412) 367-3003 or Fax (412) 367-4373 and ask for the Short Course Office to request a copy of the short course brochure and information about student scholarships

RESEARCH SOCIETY

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1993 FALL MEETING SESSION LOCATOR

		Monday, November 29			Tuesday, November 30		
Activity	Location	a.m.	p.m.	eve*	a.m.	p.m.	eve
AA. Atomic Scale Imperfections	Salon C/D (M)	AA1: Point Defects	AA2: Diffusion		AA3: Grain Boundaries	AA4: Interfaces 1	
A. Ion Beams Synthesis & Processing	America South (W)	A1: Ion Beam Processing A2: Beam-Induced Damage & Recovery—Silicon	A3: Beam-Induced Damage & Recovery/Semiconductors A4: Other Materials	Posters A5	A6: Modification of Optical Properties A7: Materials Synthesis	A7: Materials Synthesis A8/D3: Ion Beam Synthesis of Silicides	Posters A9
B. Thin Film Evolution	America North (W)	B1: Atomistics	B2: Interface & Surface Structure		B3: Kinetic Roughening	B4: Islanding & Coarsening	Posters B5
Ca. Interface Control of Properties	Essex Center (W)	Ca1: Interface Properties	Ca2: Silicon Oxidation		Ca3: Metal/Semiconductor Contacts	Ca4: Heteroepitaxy	
Cb. Defect-Interface Interactions	Essex East (W)		Cb1: Heterostructures I		Cb2: Heterostructures II	Cb3:Interfaces & Point Defects	
D. Silicides, Germanides & Interfaces	St. George C/D (W)		D1: Applications, Contacts & Devices		D2: Fabrication & Properties of Iron Silicides America South (W)	D3/A8: Ion Beam Synthesis of Silicides	Posters D4
E. Amorphous Materials Crystallization	America Center (W)	E1: Structure of Glasses I	E2: Structure of Glasses II E3: Structural Relaxation of Glasses		E4: Crystal Nucleation E5: Solid State Amorphization	E6: Crystallization Kinetics	Posters E7, E8, E9, E10
F: High-Temperature Silicides/ Refractory Alloys	Salon A/B (M)	F1: Silicide Microstructures	F2: Silicide Synthesis & Processing		F3: Silicide Mechanical Behavior	F4: Silicide Oxidation/ Properties	Posters F5
G. Fullerenes	Salon F (M)	G1: Formation & Separation	G2: Physical & Structural Properties	Posters G3	G4: Superconductivity & Electronic Structure	G5: Superconductivity & Electronic Structure	Posters G6
H, Superconductivity	Salon G (M)	H1: Bulk Applications	H2: Bulk J _C	Posters H3	H4: Fundamental Mechanisms	H5: Flux Pinning & Dynamics	Posters H6
I. Materials Processes for Manufacturing	Essex West (W)		entraliana Angusta Salahanan			Robinsport scale Solot Landard St	
J. Electronic Packaging	Theater	J1: Low-Cost High- Performance Packages	J2: Deposition & Durability		J3: Environmentally Sound Materials J4: New Materials	J5: Supercomputer Applications	Posters J6
K. Semiconductor Materials Processing	Essex West (W)	K1: Modulation Spectroscopy & Reflectivity	K2: Ellipsometry		K3: IR & Raman Spectroscopy	K4: Processing Diagnostics I	
L. Defects in Semiconductors	Essex North Center (W)	L1: Defects in Quantum Wells & Superlattices	L2: Defects & Impurities in InP, SiGe/Si		L3: Doping & Defects in III-V Semiconductors	L4/M5: Semiconductor Alloys & Superlattices Staffordshire (W)	Posters L5
M. Semiconductor Heterostructures	Staffordshire (W)	M1: Epitaxy I	M2: Epitaxy II	Posters M3	M4: Quantum Wires & Dots	M5/L4: Semiconductor Alloys & Superlattices	
N. Covalent Ceramics: Non-Oxides	Theatre	N1/Y1: MOCVD of Non-Oxide Electronic Ceramics	N2: Copper Indium Diselenide for Photovoltaics N3: Fundamental Properties	Posters N4	N5: Interfaces & Composites	N6: Metal Sulfides	Spiller
O. Complex Fluids	Salon J/K (M)	01: Surfactant Phases	02: Lamellar Phases		03: Membranes: Micelles	04: Strongly-Interacting Polymers	
P. Fractals, Scaling & Dynamics	Provincetown/ Orleans (M)		P1: Patterns, Instabilities & Noise		P2: Granular Dynamics	P3: Pinning & Slow Relaxation	Posters P4
Q. Organic Solid State Materials	Essex South (W)	Q1: Plenary Session	Q2: Conducting Polymers		Q3: Molecular Engineering	Q4: Nonlinear Optical Polymers	Posters Q5
R. Materials for Solid State Lasers	Regis (M)	R1: Infrared Nonlinear Optical Materials R2: Bulk NLO Crystals	R3: Melt Growth of Laser Crystals R4: High Power Laser Materials	Posters R5:	R6: Nonlinear Waveguide Materials R7: Up-Conversion & Visible Laser Materials	R8: MID-IR Laser Materials R9: Theoretical Modeling of Laser Materials	NGP (CC)
S. Biomolecular Materials by Design	Yarmouth/ Vineyard (M)	S1: Nanostructures	S2: Nanostructures—Silk/ Other Fibers		S3: Nanostructures	S4: Crystallography	anangtar A sassaits
T. Biomaterials for Drug & Cell Delivery	Cape Cod/ Hyannis (M)	T1: Tissue Scaffolding & Regeneration	T2: Genetic Engineering		T3: Cell-Biomaterial Interactions	T4: Biomacromolecular Controlled Delivery	
U: Nanoscale Properties	Salon H/I (M)		U1: Local Spectroscopy & Imaging		U2: Dynamic Properties at Nanoscale	U3: Local Structures & Properties	Posters U4
V. Nuclear Waste Management	Salon E (M)	V1: High-Level Nuclear Waste Glass	V2: HLW Glass Characteristics		V3: Objectives & Limitations V4: Radiation Effects & Gas Generation	V5: Ceramic Materials V6: Cementitious Materials	74597
W. Gas-Phase Surface Chemistry in Electronic Materials	Theatre	W1: Silicon & Carbon Systems	W1: Silicon & Carbon Systems	Posters W2, W3, W4	W5: III-V Semiconductors	W5: III-V Semiconductors W6: II-VI Semiconductors	Posters W7, W8, W9
X. Frontiers of Materials Research	Salon E (M)		X1		Taken and the same		
Y. MOCVD of Electronic Ceramics	Theatre	Y1/N1: MOCVD of Non-Oxide Electronic Ceramics	Y2: Ferroelectric Materials	Posters Y3	Y4: Modeling	Y5: Precursor Design & Delivery	

A10: Panel Discussion A12: B6: Stress & Defects Ca5: Surfaces Cb4: Boundary Migration, Transformation & Kinetics D5: Surfaces & Interfaces E11: Crystallization Microstructure: Polymers F6: Refractory Alloys & Processing G7: Chemistry G8: Ti H7: Vortex Dynamics K5/M6: Characterization of Epitaxial Material Staffordshire (W) L6: Oxygen, Hydrogen & Other Impurities Ter	p.m. AG: Mechanical Aspects of Interfaces 1: Ion Implantation Doping of Silicon 2: Ion Implantation Doping of Materials 37: Adsorbates in Growth Ca6: Film Stability Cb5: Boundary Migration, ransformation & Kinetics D6: Metals on Ge & SiGe E12: Crystallization Microstructure F7: Refractory Alloys Thin Films & Photophysics H8: Microstructure of uperconducting Materials 9: New Mercury Cuprates 1: Performance Measures	Posters Cb6	A14/E13: Beam Assisted Crystallization & Amorphization B8: Zone Models/Grain Growth Ca7: Interfaces in Composites Cb7: Grain Boundary/ Dislocation Interactions I D7: Kinetics of Silicide Formation E13/A14: Beam-Assisted Crystallization & Amorphization America South (W) F8: Refractory Alloys G9: Onions, Spheroids & Endofullerenes H11: Device Applications 12: Process Development for Factories Salon C/D (M) J9: Mechanical Testing	December 2 p.m. A15: Ion Implantation A16: Thin-Film Growth B9: Texture in Polycrystalline Films Ca8: Surface & Interfaces Analyses Ca9: Thin Films & Bilayers Cb8: Grain Boundary/ Dislocation Interactions II D8: Novel Silicide Growth Techniques D9: Properties & Silicides E14: Crystallization of Amorphous Silicon E15: Interfacial Phenomena F9: Applications of Refractory Alloys G10: Tubes & Capsules H12: Materials Issues in Devices I3: Process Development for Factories Salon C/D (M)	Posters A17 Posters B10 Posters Ca10, Ca11, Ca12, Ca13 Posters E16, E17, E18 Posters H13	A18: Low-Energy Ion Technology A19: Low-Energy Ion Effects B11: CVD & Ion Assisted Growth Ca14: Ferroelectrics Ca15: Stress & Adhesion	p.m.
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N7: Microstructrual Evolution N8	N8: Chemical Synthesis		N9: Transition Metal Carbides & Nitrides/Thin Films N10: Bulk Material				
O5: Monolayers O6: M	Monolayers: Liquid Crystals	Posters: 07	08: Complex Fluids in Flows	09: Colloids		010: Wetting Phenomena	
P5: Flux Line Dynamics P6: Fractal Growth & Aggregation	P7: Porous Media	Posters P8	P9: Dynamics of Rough & Fractal Surfaces	P10: Phase Separation & Cellular Patterns			
.Q6: Molecular Engineering Q8: Q7: Third Order Nonlinear Opt. Matls	8: Liquid Crystal Displays	Posters Q9	Q10: Light Emitting Diodes Q11: Organic Ferromagnets	Q12: Nonlinear Optical Materials		Q13: Nonlinear Optics— Measurements Salon F (M)	Q14: Con- ducting Polyme Salon F (M)
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T5: Biomaterials Characterization	(00) (0)						atoridio
U5: Composition Determination U	U6: Elemental Imaging		U7: Molecular Imaging	U8: Surface Structures & Physical Properties	Posters U9	U10: 3D Imaging at Atomic Resolution	
V7: Actinides & Spent Fuel V8: Glass Processing & Properties Dis	V9: Glass Leaching, Dissolution & Alteration	Posters V10	V11: Natural & Ancient Analogues V12: Tru Wastes & Special Topics	V13: Sorption Mechanisms V14: Repository Studies V15: Geochemistry & Hydrology		V16: Containers V17: Backfill Materials	
W10: Metallization	W11: Dielectics		W12: Etching	W13: Special Topics			
	X2			Х3			
Y6: High T _c Superconductors Y7: 0							

MRS EXHIBIT

Boston Marriott Hotel Tuesday-Thursday, November 30 – December 2, 1993

As part of the 1993 Fall Meeting, a major exhibit will be held to display analytical and processing equipment closely paralleling the nature of the technical symposia. The exhibit will be in the Boston Marriott Hotel and a table-top display on the fourth floor of the Westin Hotel. The technical program has been arranged to allow meeting participants ample opportunity to visit the exhibit.

Exhibit Hours

Coffee will be available during morning and afternoon breaks in the Exhibit area, Tuesday afternoon through Thursday morning.

Partial List of 1993 Fall Meeting Exhibitors

Academic Press, Inc. ACS/Office of Industry Relations Advanced Control Systems Corp. **AET Thermal** Aixtron Inc. AJA International American Chemical Society American Institute of Physics Anatech, Ltd. APD Cryogenics Inc. Applied Science & Technology, Bal-Tec Products, Inc. Balzers Blake Industries, Inc. Butterworth-Heinemann Cambridge University Press Ceramaseal Chapman & Hall CI Systems Inc. Commonwealth Scientific Corp. Conductus **CRYO** Industries of America Cryomech, Inc. Danfysik/GMW Denton Vacuum, Inc. Digital Instruments, Inc. Elsevier Science Publishing Company, Inc. **Emcore Corporation** Evans East, Inc. E. A. Fischione Instruments.Inc.

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